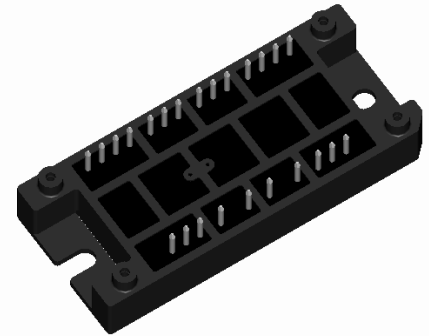
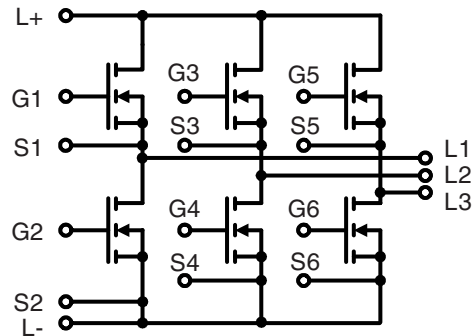


## Three phase full bridge with Trench MOSFETs

$$V_{DSS} = 100 \text{ V}$$

$$R_{DSon} = 3.6 \text{ m}\Omega$$

$$I_{D25} = 210 \text{ A}$$



### MOSFETs

| Symbol    | Conditions  | Maximum Ratings |   |
|-----------|---|-----------------|---|
| $V_{DSS}$ | $T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$ | 100             | V |
| $V_{GS}$  |   | $\pm 20$        | V |
| $I_{D25}$ | $T_C = 25^{\circ}\text{C}$                            | 210             | A |
| $I_{D80}$ | $T_C = 80^{\circ}\text{C}$                            | 170             | A |
| $I_{D25}$ | $T_C = 25^{\circ}\text{C}$ (diode)                    | 210             | A |
| $I_{D80}$ | $T_C = 80^{\circ}\text{C}$ (diode)                    | 170             | A |

### Applications

AC drives

- in automobiles and trucks
  - electric power steering
  - starter generator
  - etc...

- in industrial vehicles
  - propulsion drives
  - fork lift drives

- in battery supplied equipment

| Symbol       | Conditions  | Characteristic Values<br>( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified) |      |      |
|--------------|---|--|------|------|
|              |   | min.   | typ. | max. |
| $R_{DSon}$   | $V_{GS} = 10 \text{ V}; I_D = 100 \text{ A}$  |  | 3.6  | 5.2  |
| $V_{GSth}$   | $V_{DS} = 20 \text{ V}; I_D = 2 \text{ mA}$   | 2  |      | 4    |
| $I_{DSS}$    | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$<br>$T_{VJ} = 125^{\circ}\text{C}$ |  | 0.25 | 0.02 |
| $I_{GSS}$    | $V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$   |  |      | 0.2  |
| $Q_g$        | $V_{GS} = 10 \text{ V}; V_{DS} = 80 \text{ V}; I_D = 200 \text{ A}$   |  | 430  | nC   |
| $Q_{gs}$     |   |  | 90   | nC   |
| $Q_{gd}$     |   |  | 180  | nC   |
| $t_{d(on)}$  | $V_{GS} = 10 \text{ V}; V_{DS} = 50 \text{ V};$<br>$I_D = 50 \text{ A}; R_G = 2.7 \Omega$                     |  | 40   | ns   |
| $t_r$        |   |  | 100  | ns   |
| $t_{d(off)}$ |   |  | 260  | ns   |
| $t_f$        |   |  | 100  | ns   |
| $V_F$        | (diode) $I_F = 100 \text{ A}; V_{GS} = 0 \text{ V}$   |  | 1.0  | 1.5  |
| $t_{rr}$     | (diode) $I_F = 40 \text{ A}; -di/dt = 200 \text{ A}/\mu\text{s}; V_{DS} = 30 \text{ V}$                       |  | 100  | ns   |
| $R_{thJC}$   | with heat transfer paste  |  |      | 0.26 |
| $R_{thJH}$   |   |  | 0.51 | K/W  |

### Features

- MOSFETs in trench technology:
  - low  $R_{DSon}$
  - optimized intrinsic reverse diode
- package:
  - high level of integration
  - solder terminals for PCB mounting
  - isolated DCB ceramic base plate with optimized heat transfer

IXYS reserves the right to change limits, test conditions and dimensions.

### Module

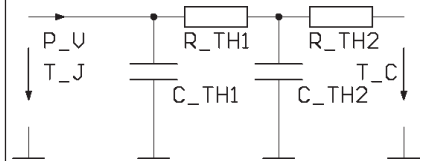
| Symbol     | Conditions  | Maximum Ratings |    |
|------------|---|-----------------|----|
| $T_{VJ}$   |   | -40...+175      | °C |
| $T_{stg}$  |   | -40...+125      | °C |
| $V_{ISOL}$ | $I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}; t = 1 \text{ min}$ | 500             | V~ |
| $M_d$      | Mounting torque (M5)  | 2 - 2.5         | Nm |

| Symbol | Conditions | Characteristic Values<br>( $T_{VJ} = 25^\circ\text{C}$ , unless otherwise specified) |      |      |
|--------|------------|--|------|------|
|        |            | min.   | typ. | max. |
| Weight | typ.       |  | 80   | g    |

### Equivalent Circuits for Simulation

#### Thermal Response

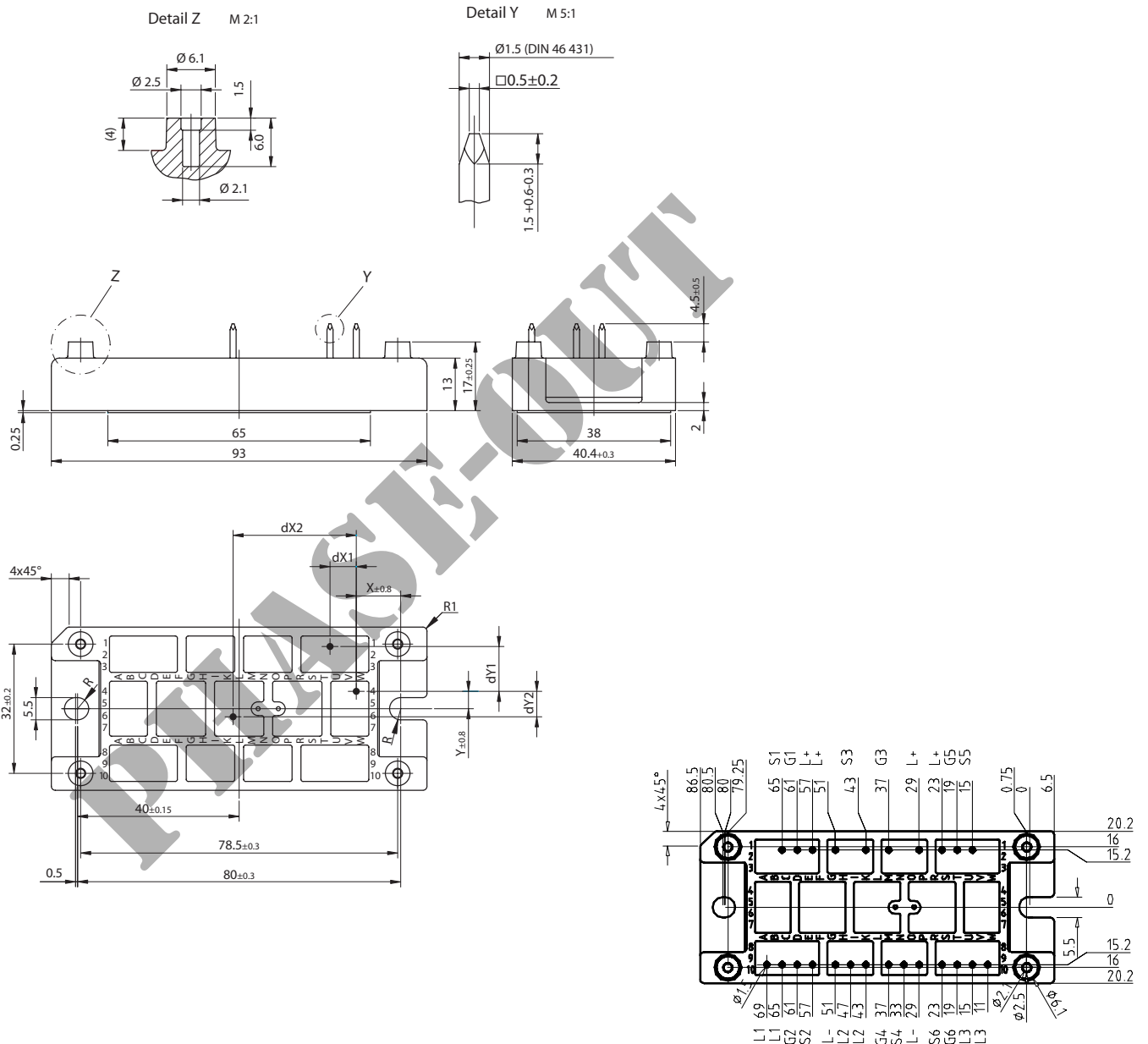


junction - case (typ.)

$$C_{th1} = 0.13 \text{ J/K}; R_{th1} = 0.08 \text{ K/W}$$

$$C_{th2} = 0.22 \text{ J/K}; R_{th2} = 0.18 \text{ K/W}$$

### Dimensions in mm (1 mm = 0.0394")



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